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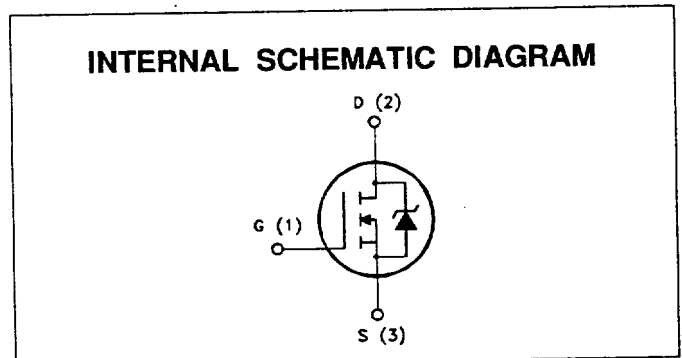
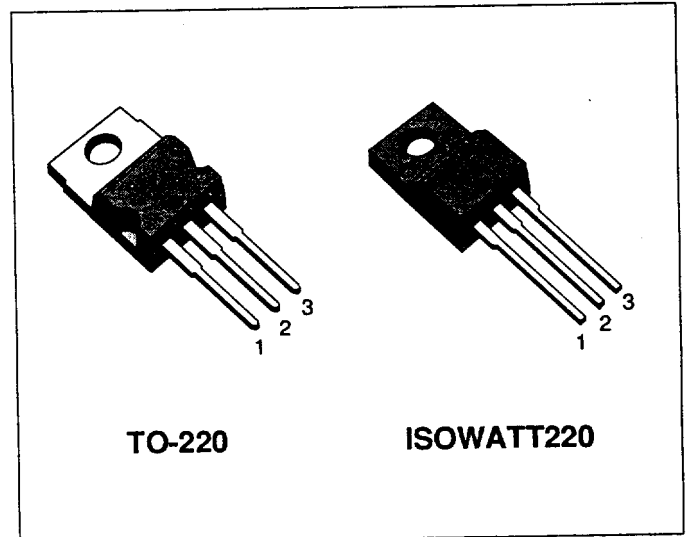
**N - CHANNEL ENHANCEMENT MODE
 POWER MOS TRANSISTOR**

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP5N90	900 V	< 2.4 Ω	5 A
STP5N90FI	900 V	< 2.4 Ω	2.8 A

- TYPICAL R_{DS(on)} = 1.9 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC INVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLY (UPS)


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP5N90	STP5N90FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	900		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	900		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	5	2.8	A
I _D	Drain Current (continuous) at T _c = 100 °C	3	1.7	A
I _{DM} (*)	Drain Current (pulsed)	20	20	A
P _{tot}	Total Dissipation at T _c = 25 °C	125	40	W
	Derating Factor	1	0.32	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(*) Pulse width limited by safe operating area

THERMAL DATA

		TC-22C	ISOWATT220	
R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	5	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	270	μJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	13	μJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	3	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 2.5 A V _{GS} = 10V I _D = 2.5 A T _c = 100°C		1.9	2.4 4.8	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	5			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 2.5 A	2	4		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1190	1450	pF
C _{oss}	Output Capacitance			165	200	pF
C _{rss}	Reverse Transfer Capacitance			70	85	pF



ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 400\text{ V}$ $I_D = 2.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		50	65	ns
t_r	Rise Time			85	105	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 640\text{ V}$ $I_D = 5.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		200		A/ μ s
Q_g	Total Gate Charge	$V_{DD} = 500\text{ V}$ $I_D = 6\text{ A}$ $V_{GS} = 10\text{ V}$		75	95	nC
Q_{gs}	Gate-Source Charge			9		nC
Q_{gd}	Gate-Drain Charge			33		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 5.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		120	150	ns
t_f	Fall Time			30	40	ns
t_c	Cross-over Time			160	200	ns

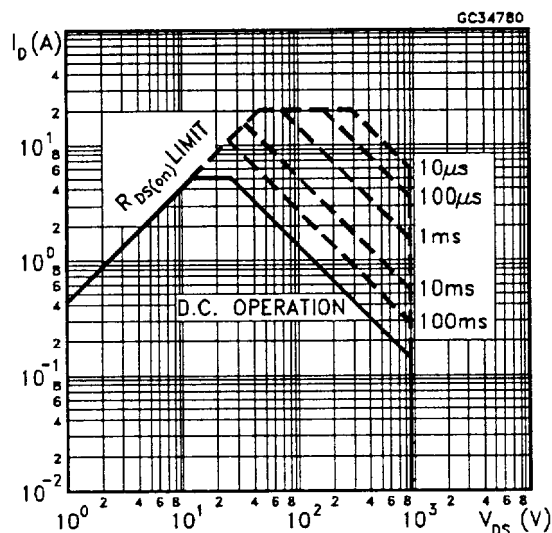
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				5	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				20	A
V_{SD}	Forward On Voltage	$I_{SD} = 5\text{ A}$ $V_{GS} = 0$			2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 5\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 80\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		700		ns
Q_{rr}	Reverse Recovery Charge				7.7	μC
I_{RRM}	Reverse Recovery Current				22	A

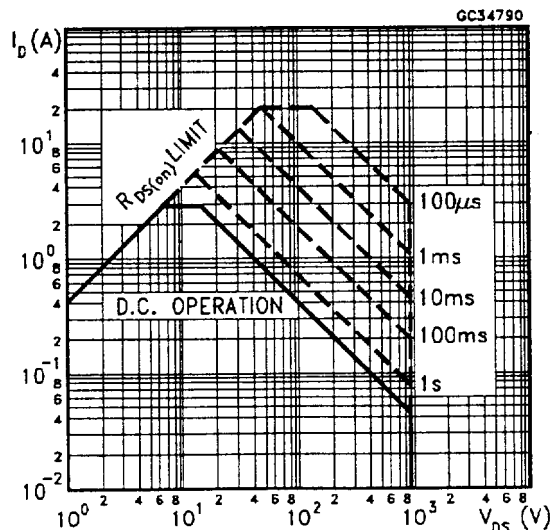
(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

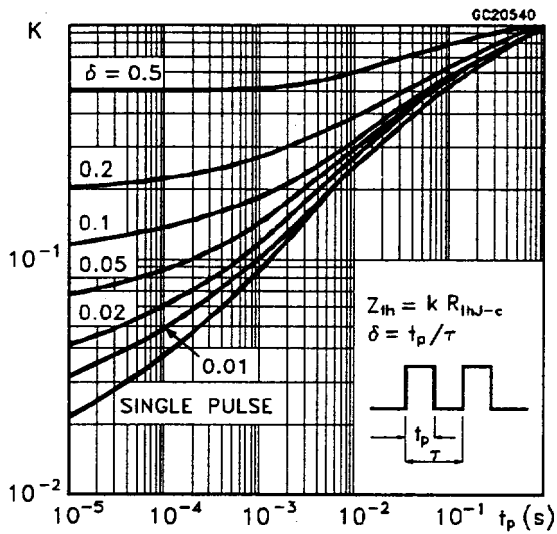
Safe Operating Areas For TO-220



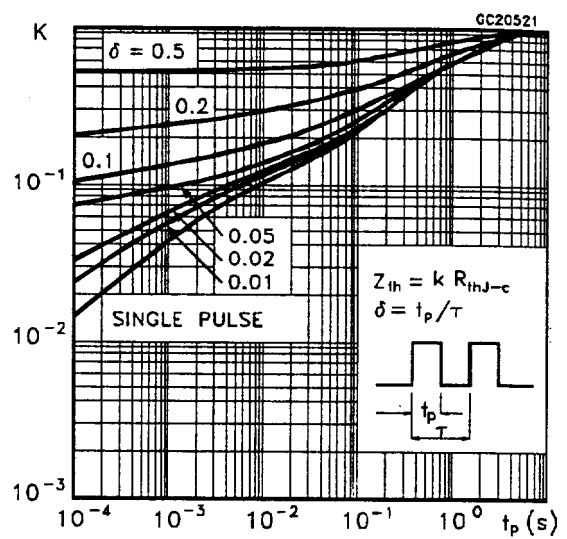
Safe Operating Areas For ISOWATT220



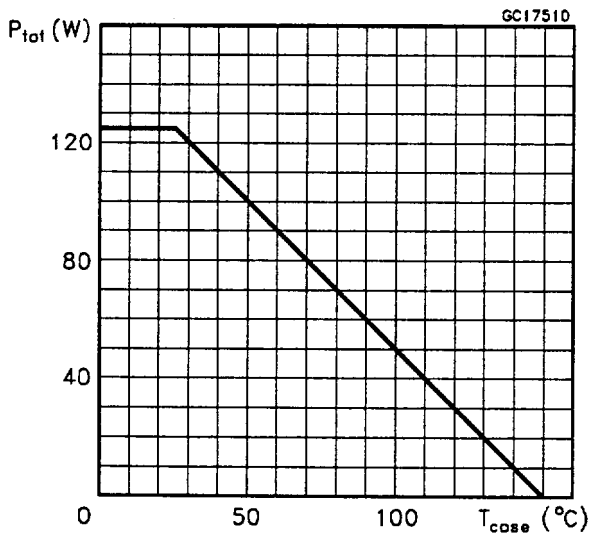
Thermal Impedance For TO-220



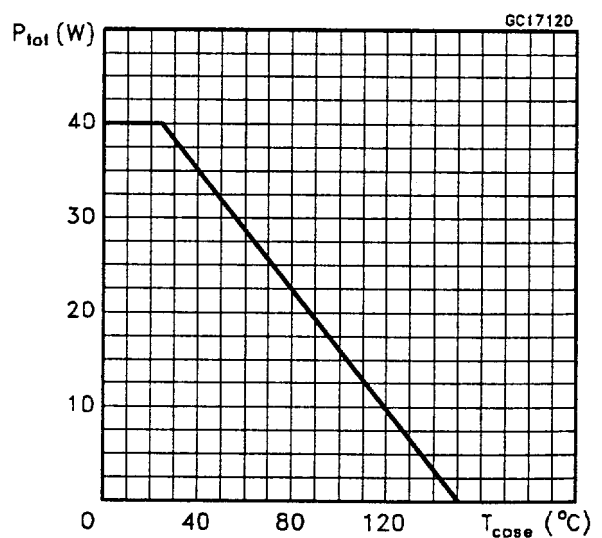
Thermal Impedance For ISOWATT220



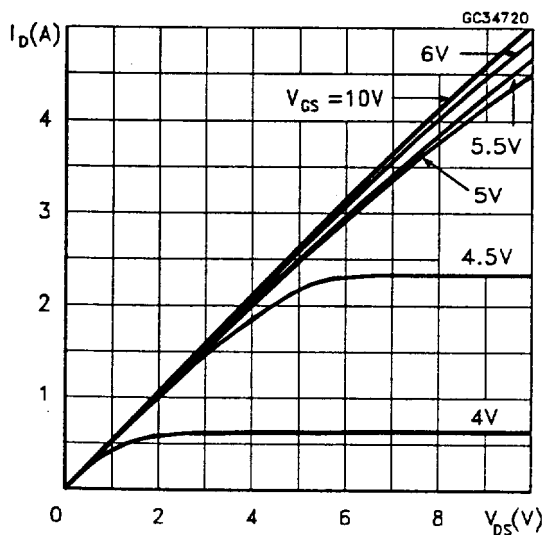
Derating Curve For TO-220



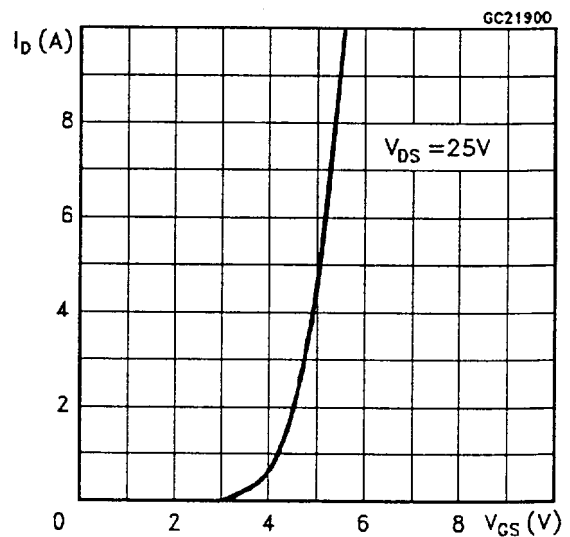
Derating Curve For ISOWATT220



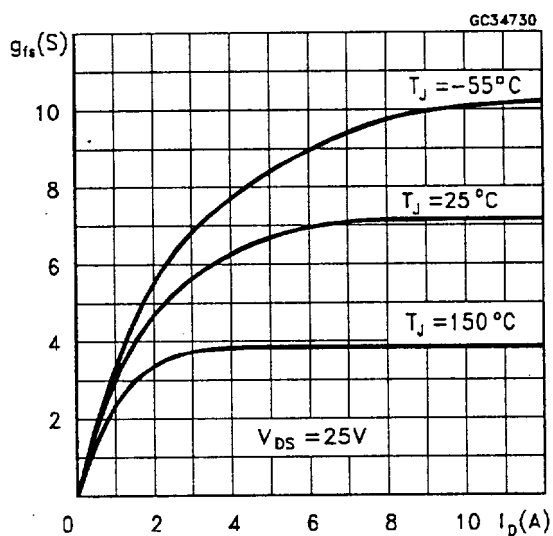
Output Characteristics



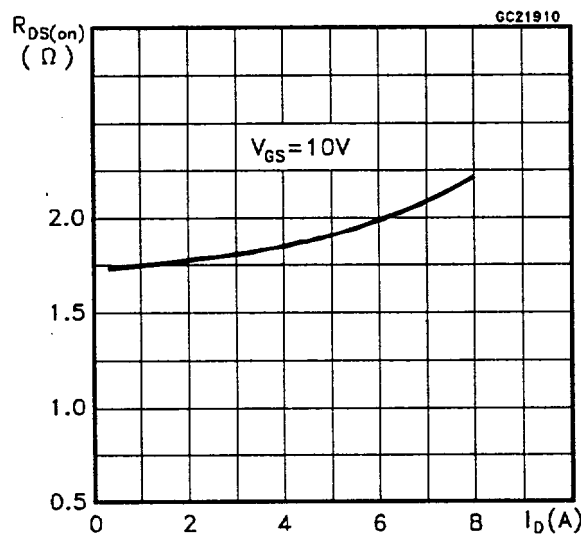
Transfer Characteristics



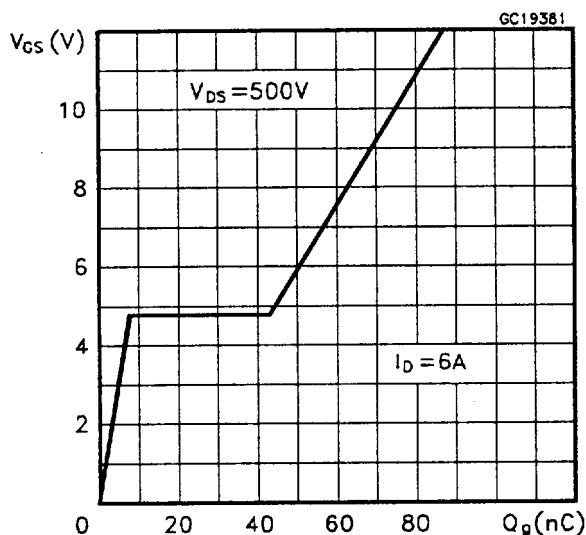
Transconductance



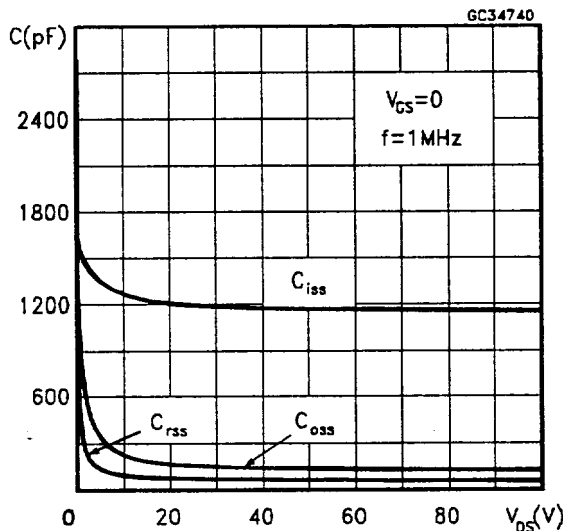
Static Drain-source On Resistance



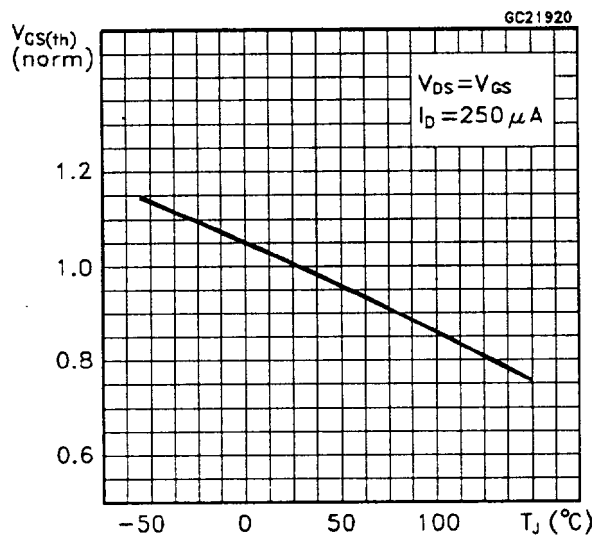
Gate Charge vs Gate-source Voltage



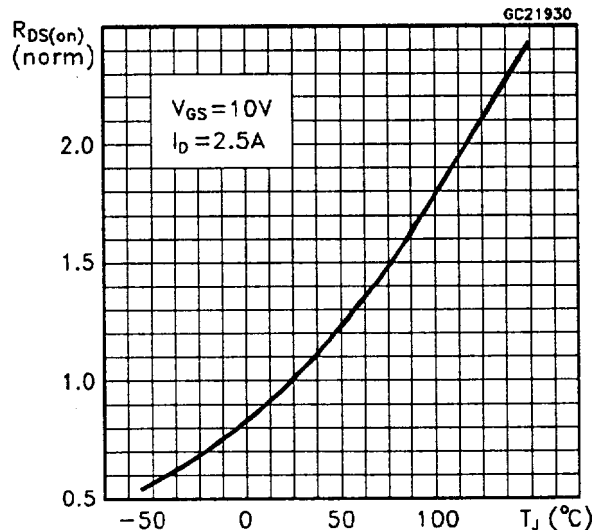
Capacitance Variations



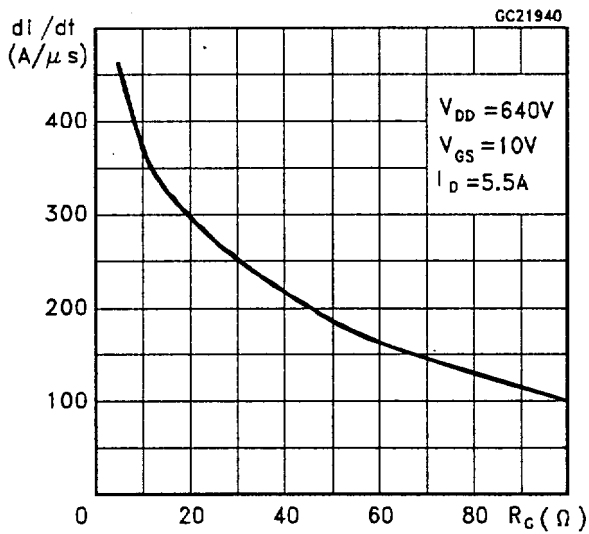
Normalized Gate Threshold Voltage vs Temperature



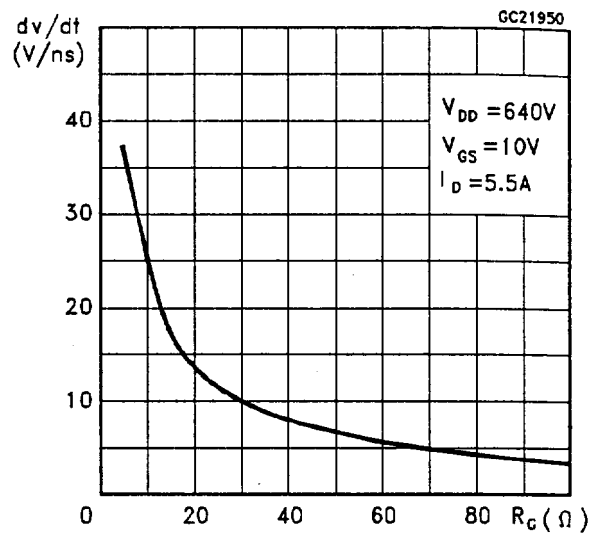
Normalized On Resistance vs Temperature



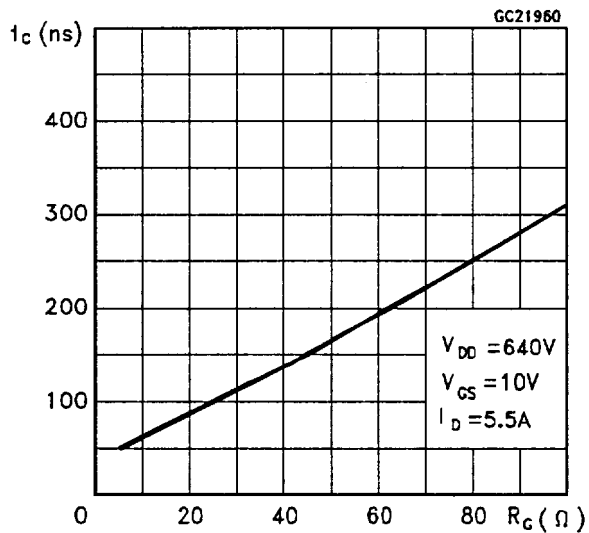
Turn-on Current Slope



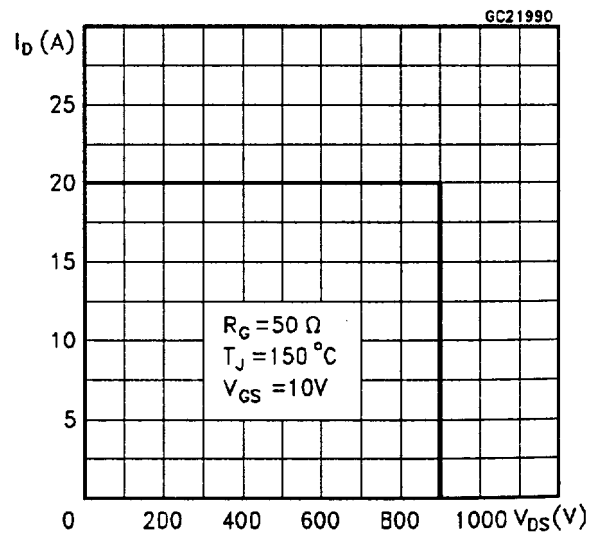
Turn-off Drain-source Voltage Slope



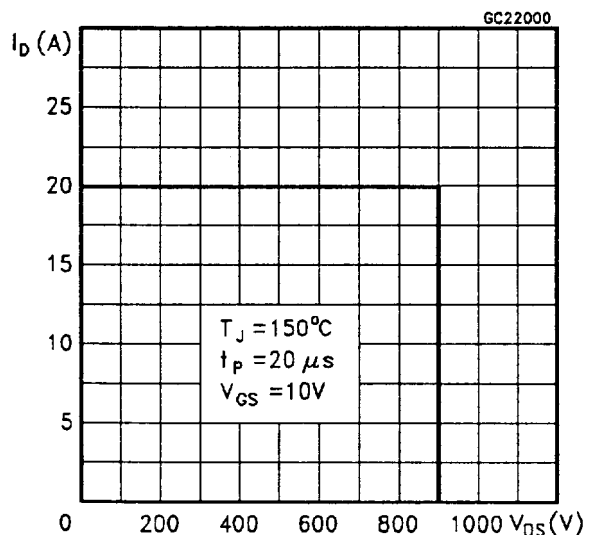
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

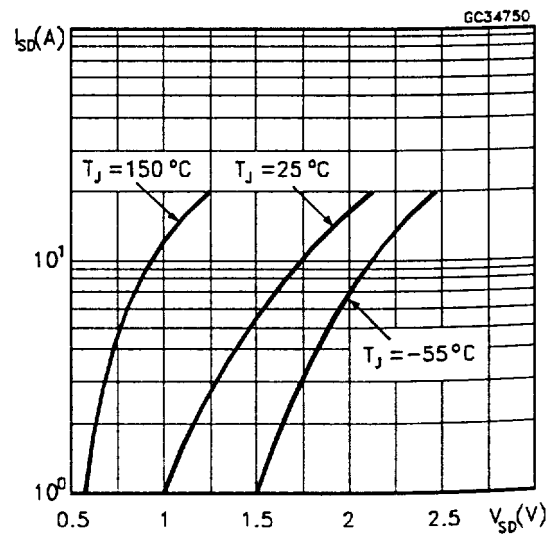




Fig. 1: Unclamped Inductive Load Test Circuits

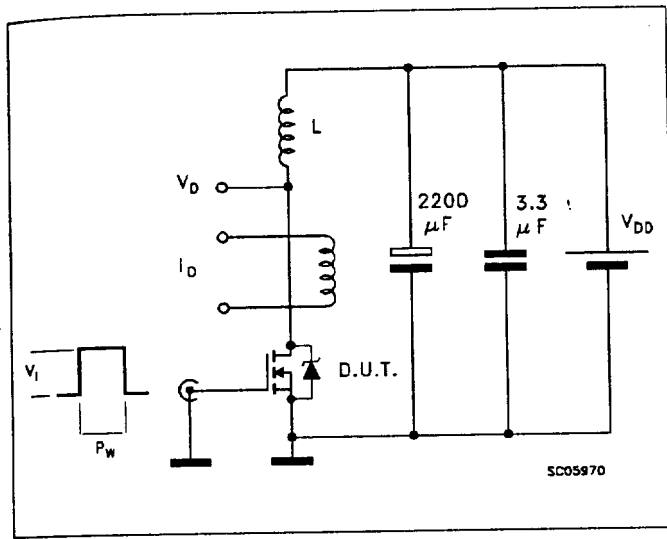


Fig. 2: Unclamped Inductive Waveforms

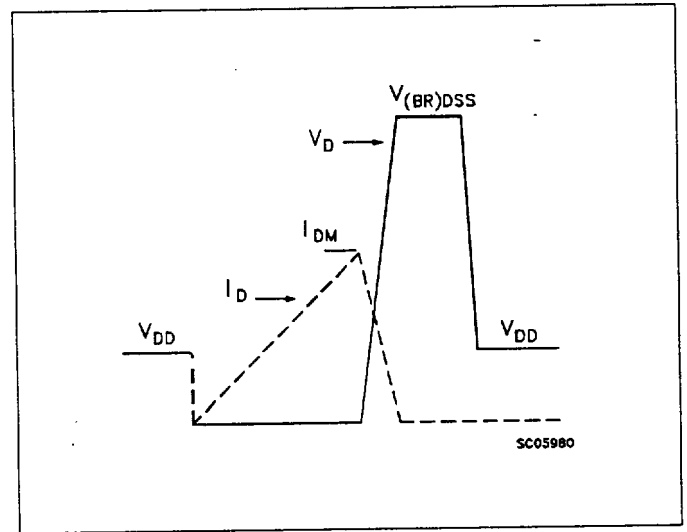


Fig. 3: Switching Times Test Circuits For Resistive Load

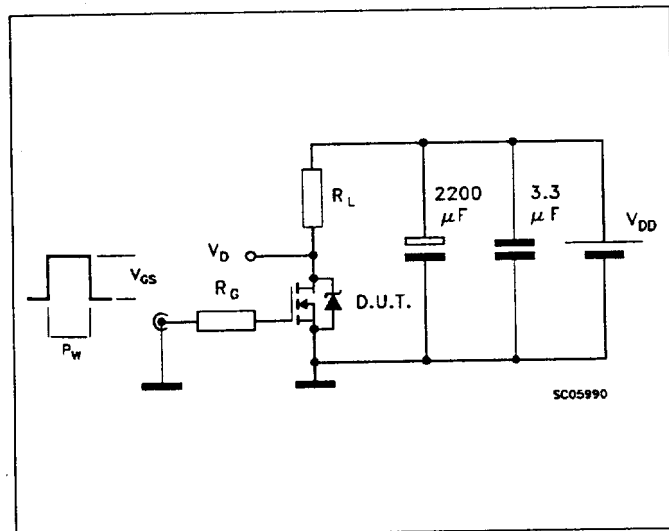


Fig. 4: Gate Charge Test Circuit

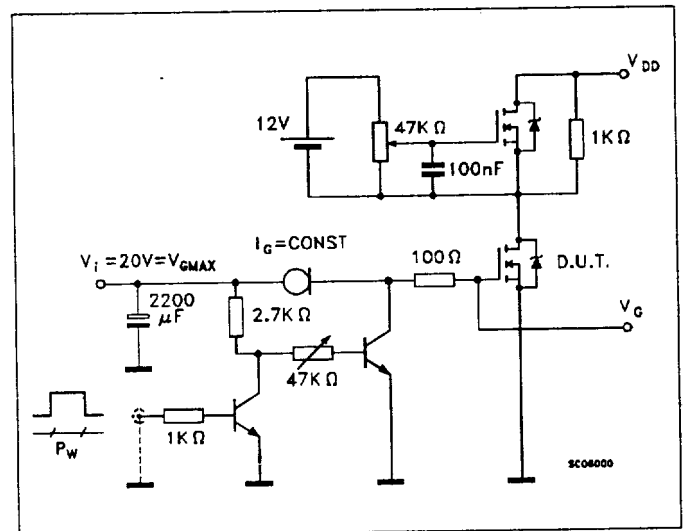


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time

